

## General Description

The WST2337A is the highest performance trench P-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the small power switching and load switch applications.

The WST2337A meet the RoHS and Green Product requirement with full function reliability approved.

## Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Green Device Available

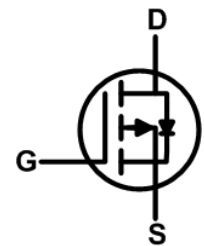
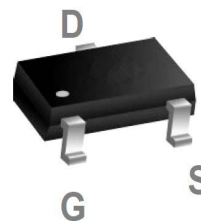
## Product Summary

BVDSS	RDSON	ID
-15V	30mΩ	-4.8A

## Applications

- High Frequency Point-of-Load Synchronous Small power switching for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

## SOT-23-3L Pin Configuration



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-15	V
$V_{GS}$	Gate-Source Voltage	$\pm 12$	V
$I_D@T_c=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -4.5\text{V}^1$	-4.8	A
$I_D@T_c=70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -4.5\text{V}^1$	-3.4	A
$I_{DM}$	Pulsed Drain Current	-24	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation <sup>3</sup>	1.4	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

## Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient <sup>1</sup>	---	125	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	80	$^\circ\text{C}/\text{W}$

**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-15	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-4.5V, I_D=-4.1A$	---	30	48	m $\Omega$
		$V_{GS}=-2.5V, I_D=-3A$	---	45	65	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-0.45	-0.7	-1.2	V
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=-12V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	-1	$\mu A$
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 12V, V_{DS}=0V$	---	---	$\pm 100$	nA
$Q_g$	Total Gate Charge	$V_{DS}=-4V, I_D=-4.1A, V_{GS}=-4.5V$	---	7.8	---	nC
$Q_{gs}$	Gate-Source Charge		---	1.2	---	
$Q_{gd}$	Gate-Drain Charge		---	1.6	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-4V, I_D=-3.3A, R_L=-1.2\Omega, V_{GEN}=-4.5V, R_g=1\Omega$	---	12	---	ns
$T_r$	Rise Time		---	35	---	
$T_{d(off)}$	Turn-Off Delay Time		---	30	---	
$T_f$	Fall Time		---	10	---	
$C_{ISS}$	Input Capacitance	$V_{DS}=-4V, V_{GS}=0V, F=1.0\text{MHz}$	---	738	1500	pF
$C_{OSS}$	Output Capacitance		---	280	---	
$C_{RSS}$	Reverse Transfer Capacitance		---	190	---	

**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous Source Current	$V_G=V_D=0V$ , Force Current	---	---	-4.1	A
$V_{SD}$	Diode Forward Voltage	$V_{GS}=0V, I_S=-1.6A, T_J=25^\circ\text{C}$	---	---	-1.2	V

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production

Typical Characteristics

Figure 1: Switching Test Circuit

Figure 2: Switching Waveforms

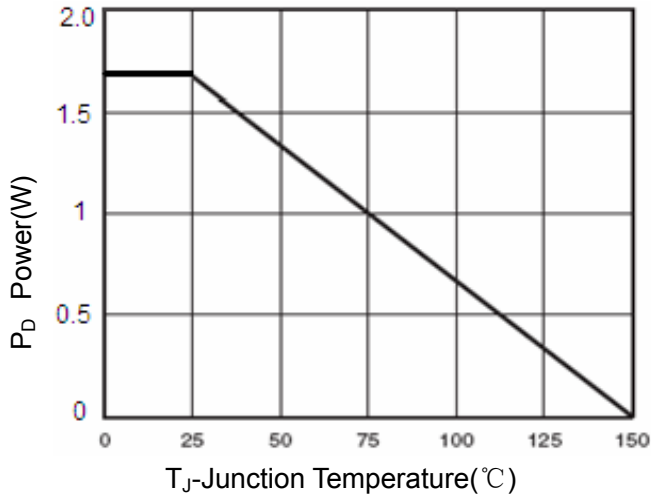


Figure 3 Power Dissipation

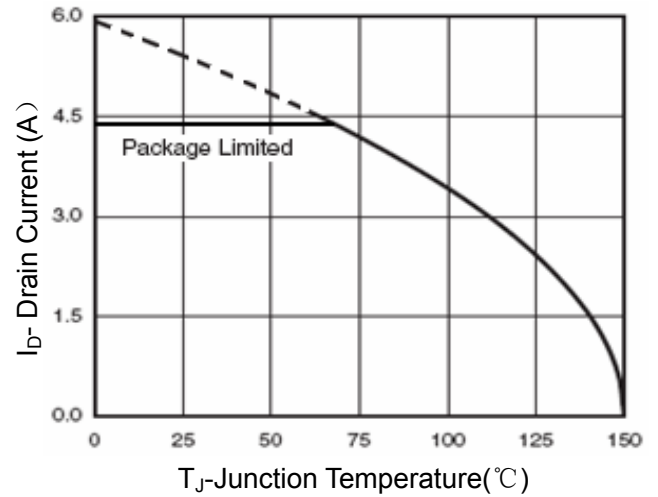


Figure 4 Drain Current

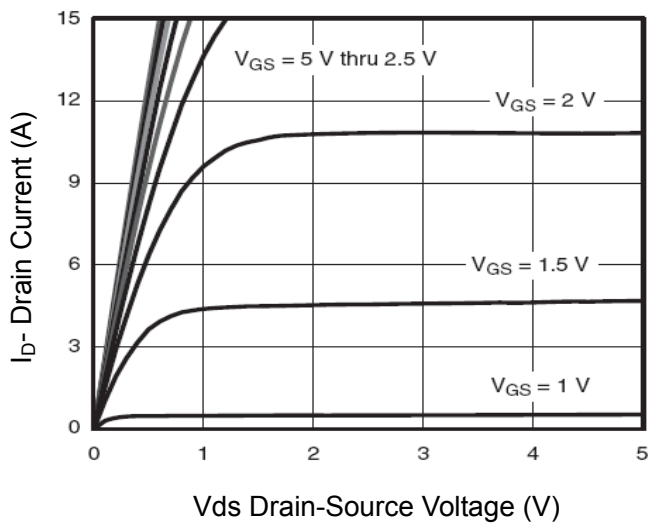


Figure 5 Output Characteristics

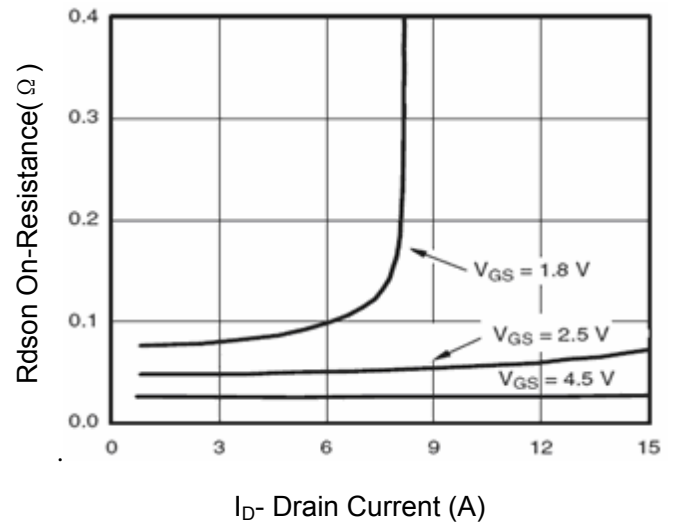
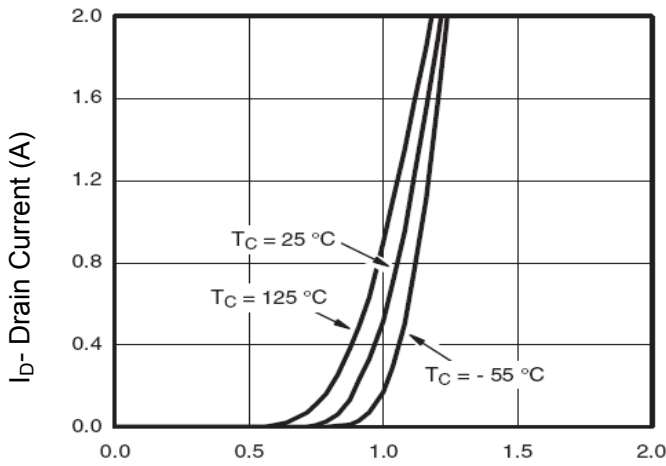
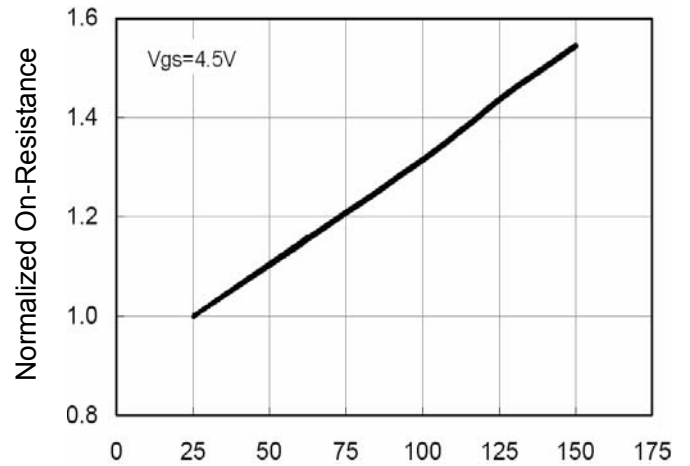


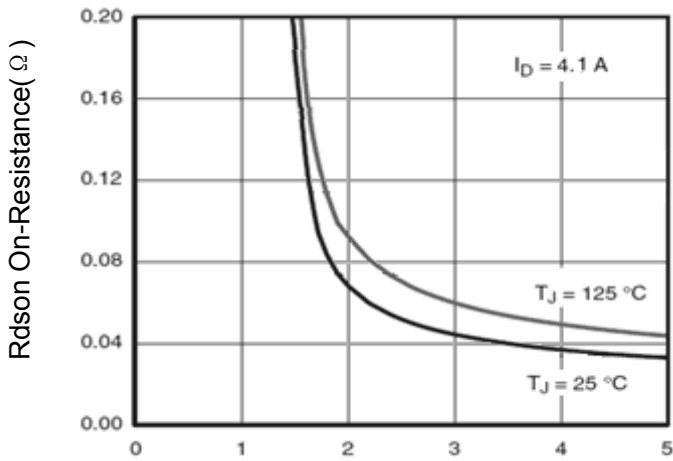
Figure 6 Drain-Source On-Resistance



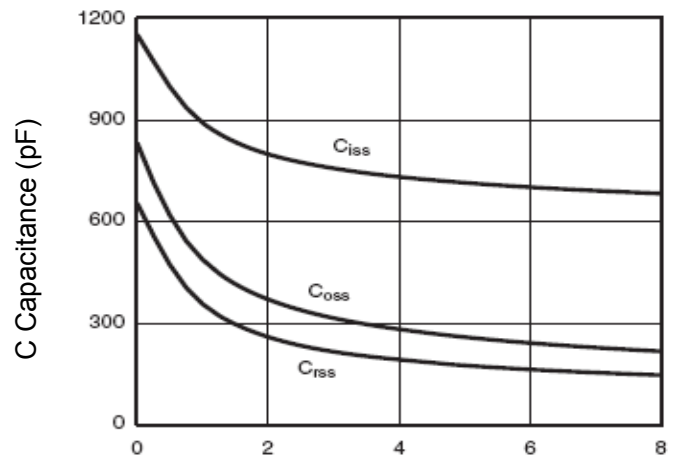
Vgs Gate-Source Voltage (V)  
**Figure 7 Transfer Characteristics**



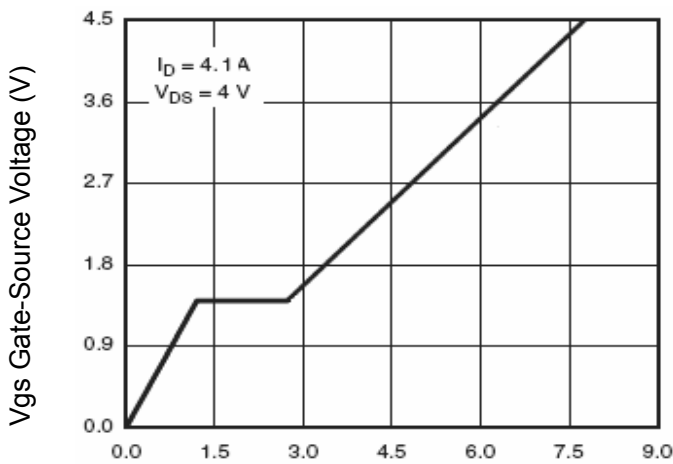
$T_J$ -Junction Temperature( $^\circ\text{C}$ )  
**Figure 8 Drain-Source On-Resistance**



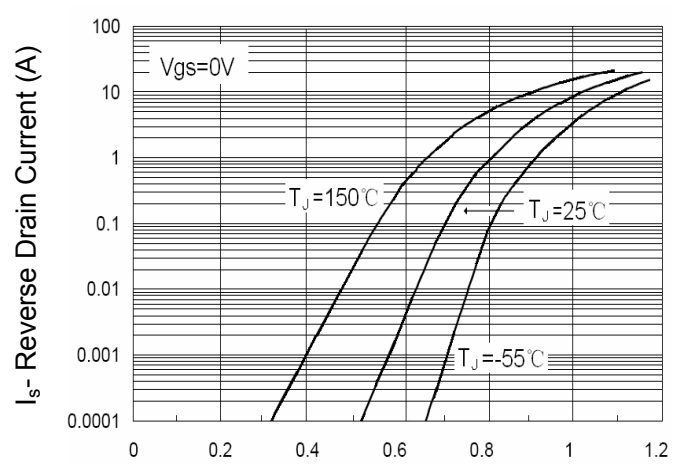
Vgs Gate-Source Voltage (V)  
**Figure 9 Rdson vs Vgs**



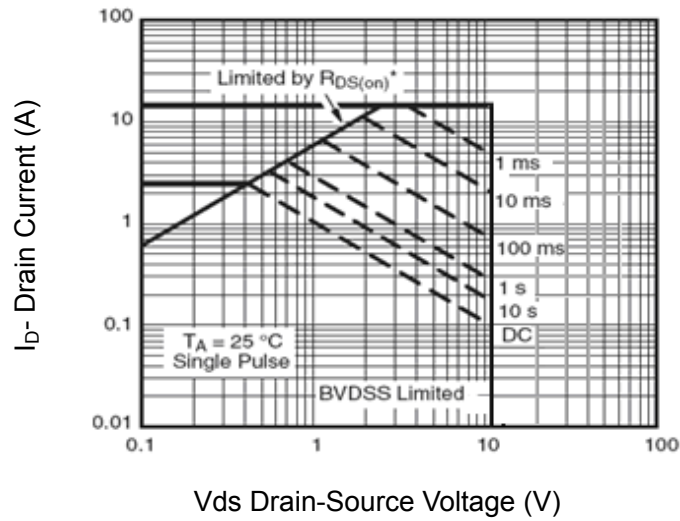
$V_{DS}$  Drain-Source Voltage (V)  
**Figure 10 Capacitance vs Vds**



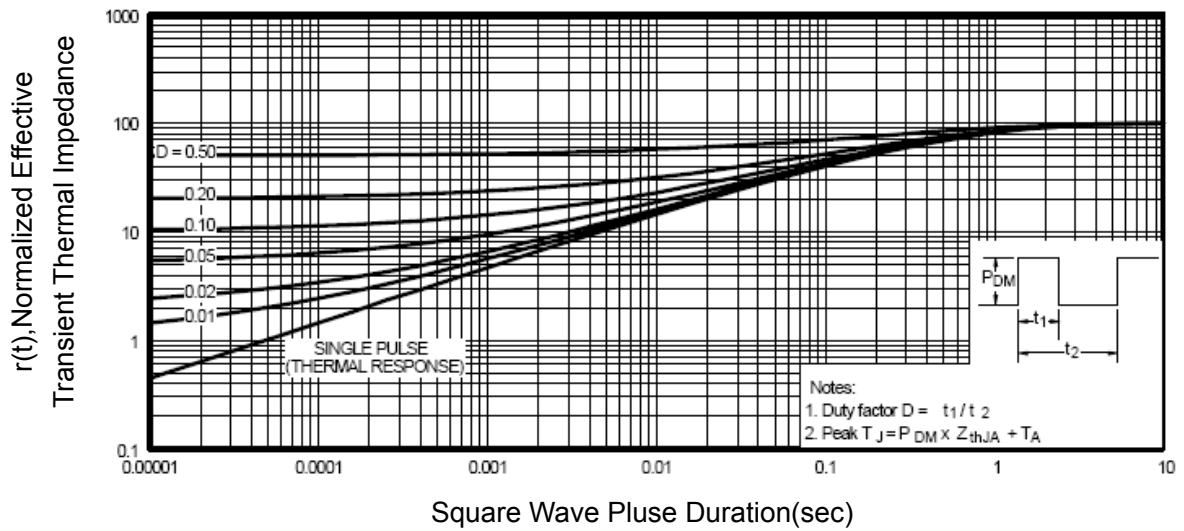
$Q_g$  Gate Charge (nC)  
**Figure 11 Gate Charge**



$V_{SD}$  Source-Drain Voltage (V)  
**Figure 12 Source- Drain Diode Forward**



**Figure 13 Safe Operation Area**



**Figure 14 Normalized Maximum Transient Thermal Impedance**



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